



D-MOSFET

MOSFET DC BIASING

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Electronics Engineer

TOPIC OUTLINE

D-MOSFET Construction

Regions of Operation

D-MOSFET DC Biasing



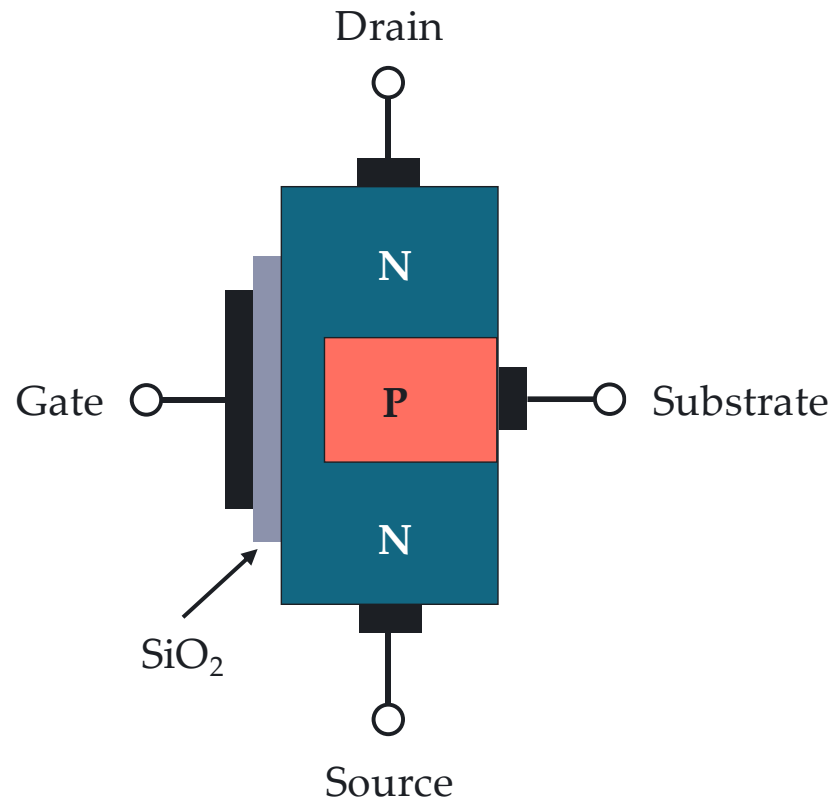
D-MOSFET CONSTRUCTION



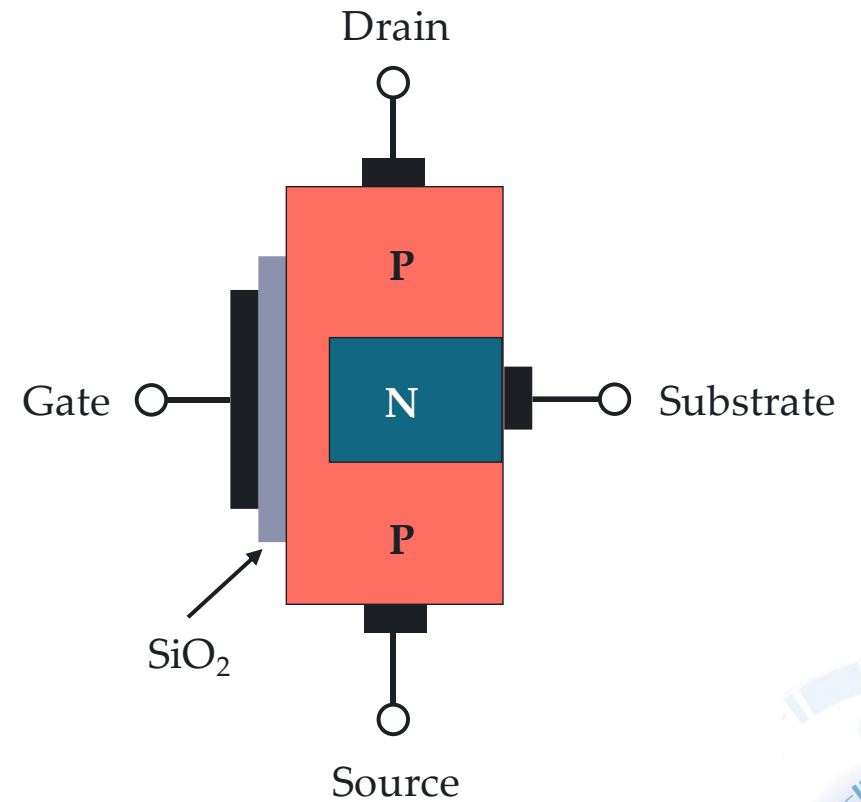
CONSTRUCTION

D-MOSFET

Depletion Mode Metal-Oxide Semiconductor Field-Effect Transistor



N-Channel

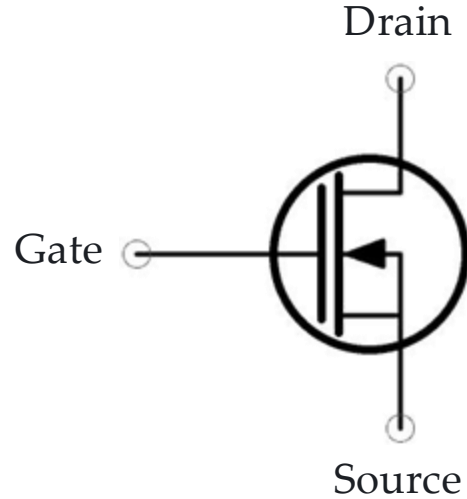


P-Channel

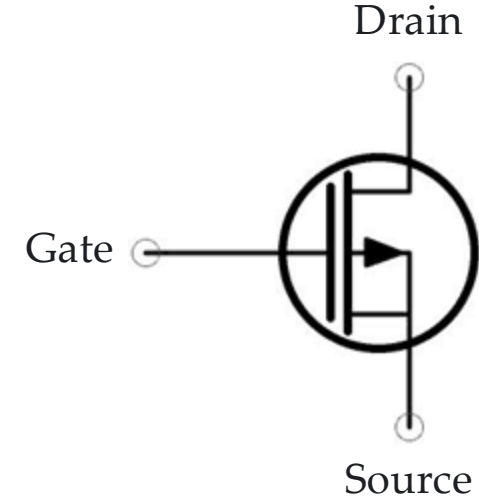
SCHEMATIC SYMBOL

D-MOSFET

Depletion Mode Metal-Oxide Semiconductor Field-Effect Transistor



N-Channel

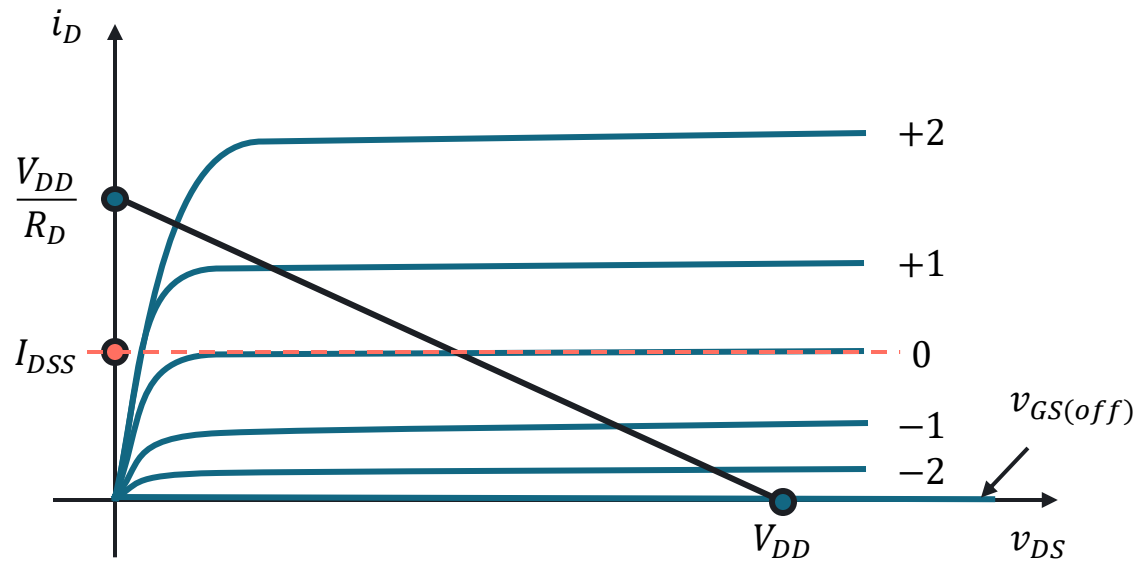


P-Channel

REGIONS OF OPERATION



DRAIN CURVE

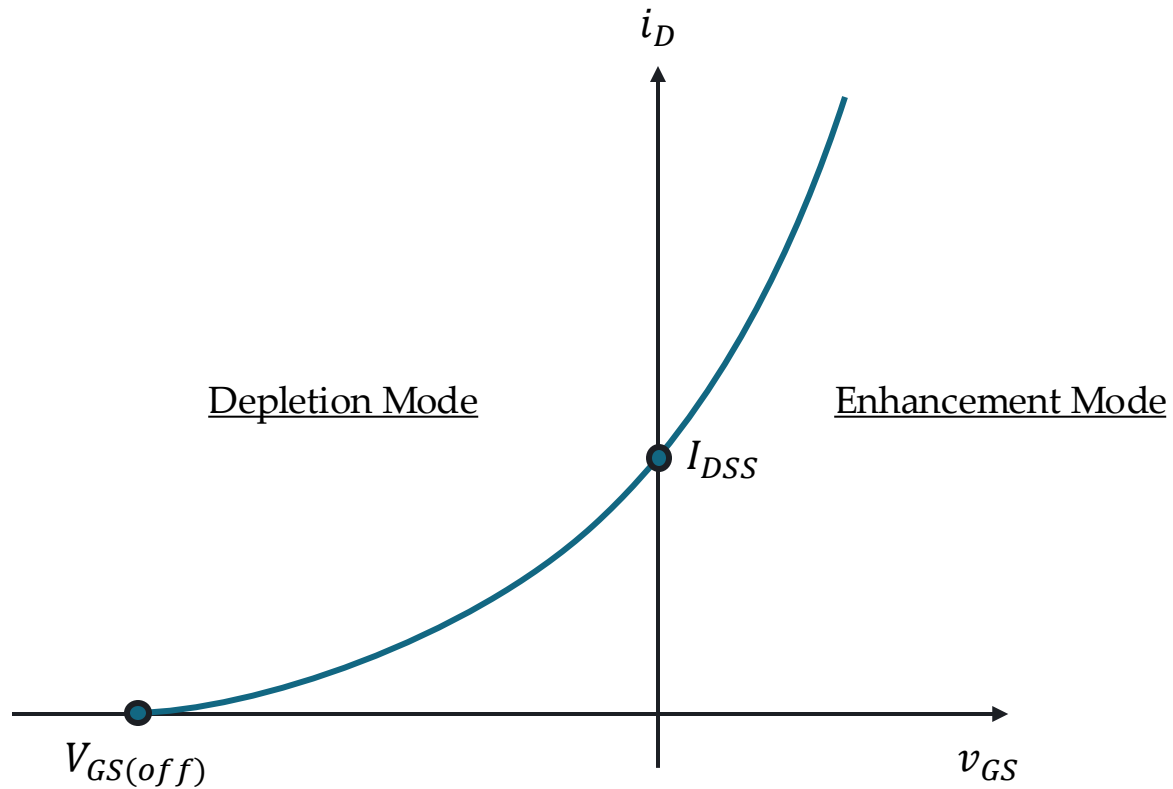


As with a JFET, when $v_{GS} = 0$ V, the drain current will equal I_{DSS} .

This demonstrates that the D-MOSFET is a **normally on** device



TRANSCONDUCTANCE CURVE



The primary difference between JFET and D-MOSFET is that D-MOSFETs permit operating points with positive values of v_{GS} and levels of i_D that exceeds i_{DSS} .

Shockley's Equation

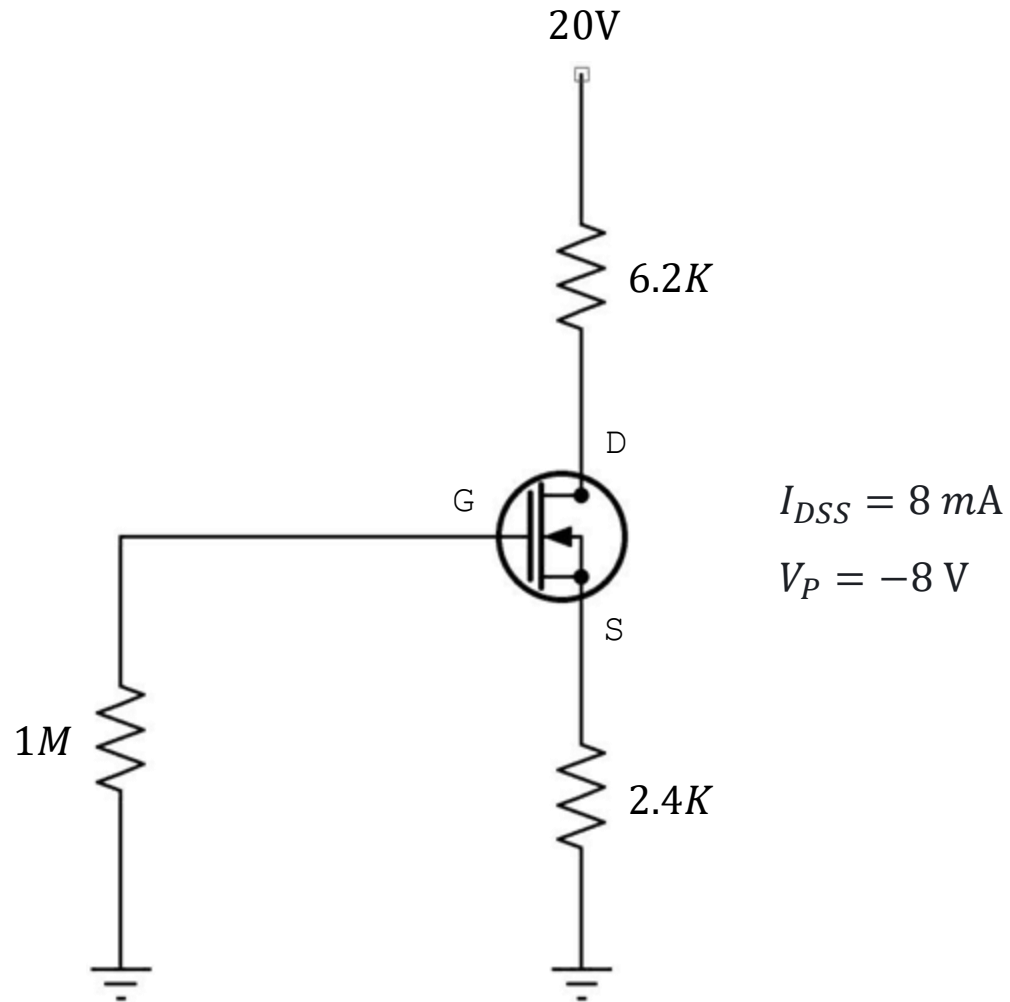
$$i_D = I_{DSS} \left(1 - \frac{v_{GS}}{V_{GS(off)}} \right)^2$$



D-MOSFET DC BIASING



EXERCISE



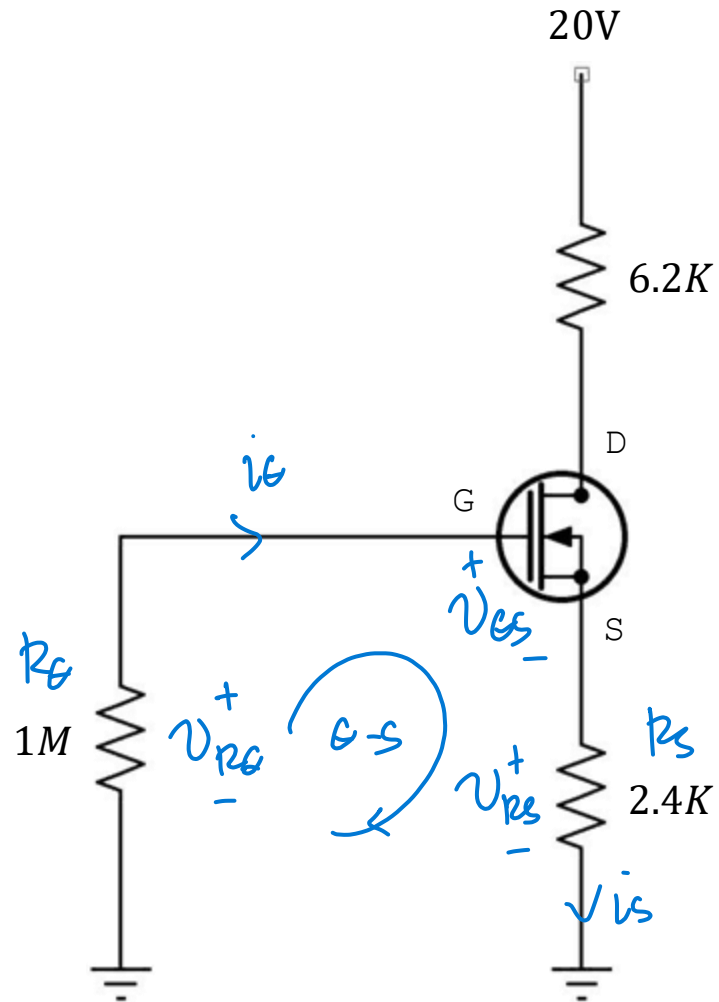
For the given network, determine the following:

- Gate-source voltage (v_{GSQ})
- Drain current (i_{DQ})
- Drain voltage (v_D)

and sketch the transconductance curve.



EXERCISE



$$I_{DSS} = 8 \text{ mA}$$

$$V_P = -8 \text{ V}$$

Solution

KVL @ G-S

$$-V_{RG} + V_{GS} + V_{RS} = 0$$

$$V_{GS} = V_{RG} - V_{RS}$$

$$V_{GS} = i_G R_G - i_S R_S$$

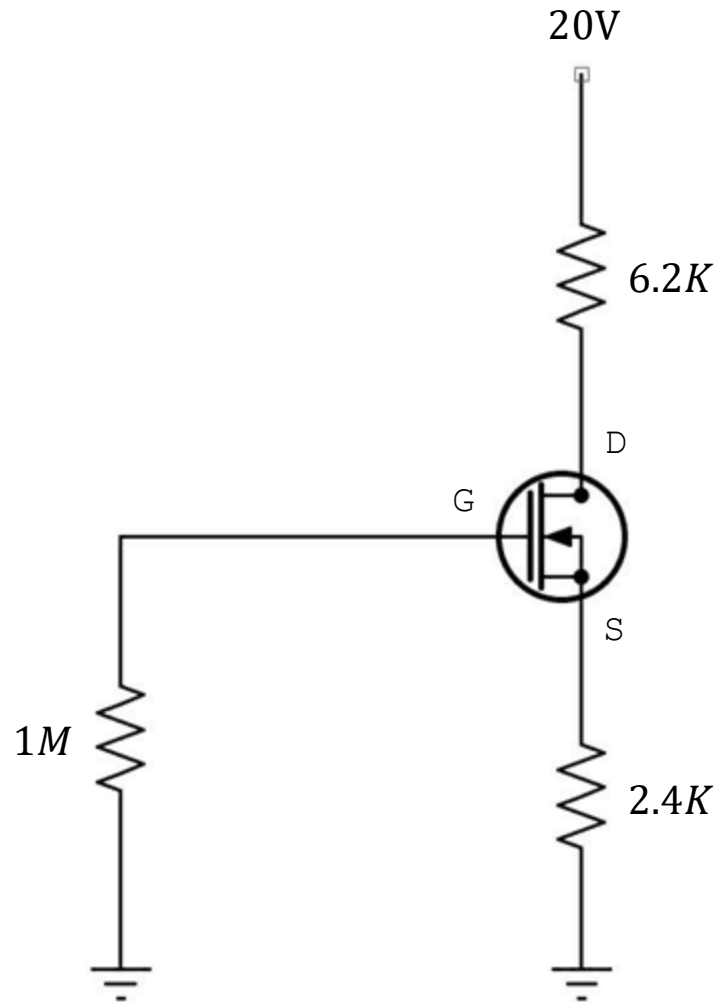
$$V_{GS} = -i_{DS} R_S$$

$$V_{GS} = -I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 R_S$$

$$V_{GS} = -I_{DSS} R_S \left(1 - \frac{2V_{GS}}{V_P} + \frac{V_{GS}^2}{V_P^2}\right)$$



EXERCISE



$$I_{DSS} = 8 \text{ mA}$$

$$V_P = -8 \text{ V}$$

Solution

$$V_{GS} = - (8\text{m} \cdot 2.4\text{k}) \left[1 - \frac{2V_{GS}}{-8} + \frac{V_{GS}^2}{(-8)^2} \right]$$

$$V_{GS} = -19.2 \left(1 + \frac{1}{4} V_{GS} + \frac{1}{64} V_{GS}^2 \right)$$

$$\cancel{V_{GS}} = -19.2 - 4.8 \cancel{V_{GS}} - 0.3 \cancel{V_{GS}}^2$$

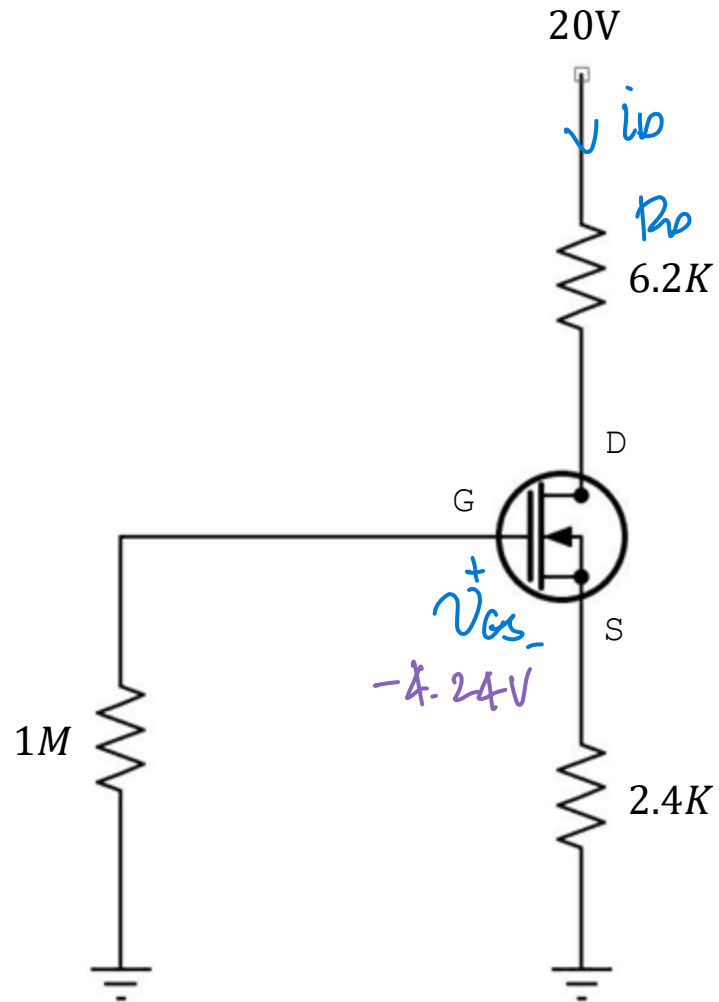
$$0 = -19.2 - 5.8 V_{GS} - 0.3 V_{GS}^2$$

$$V_{GS} = -15.09 \text{ V}$$

$$V_{GSQ} = -4.24 \text{ V}$$

ans

EXERCISE



$$I_{DSS} = 8 \text{ mA}$$

$$V_P = -8 \text{ V}$$

Solution

Shockley's Equation

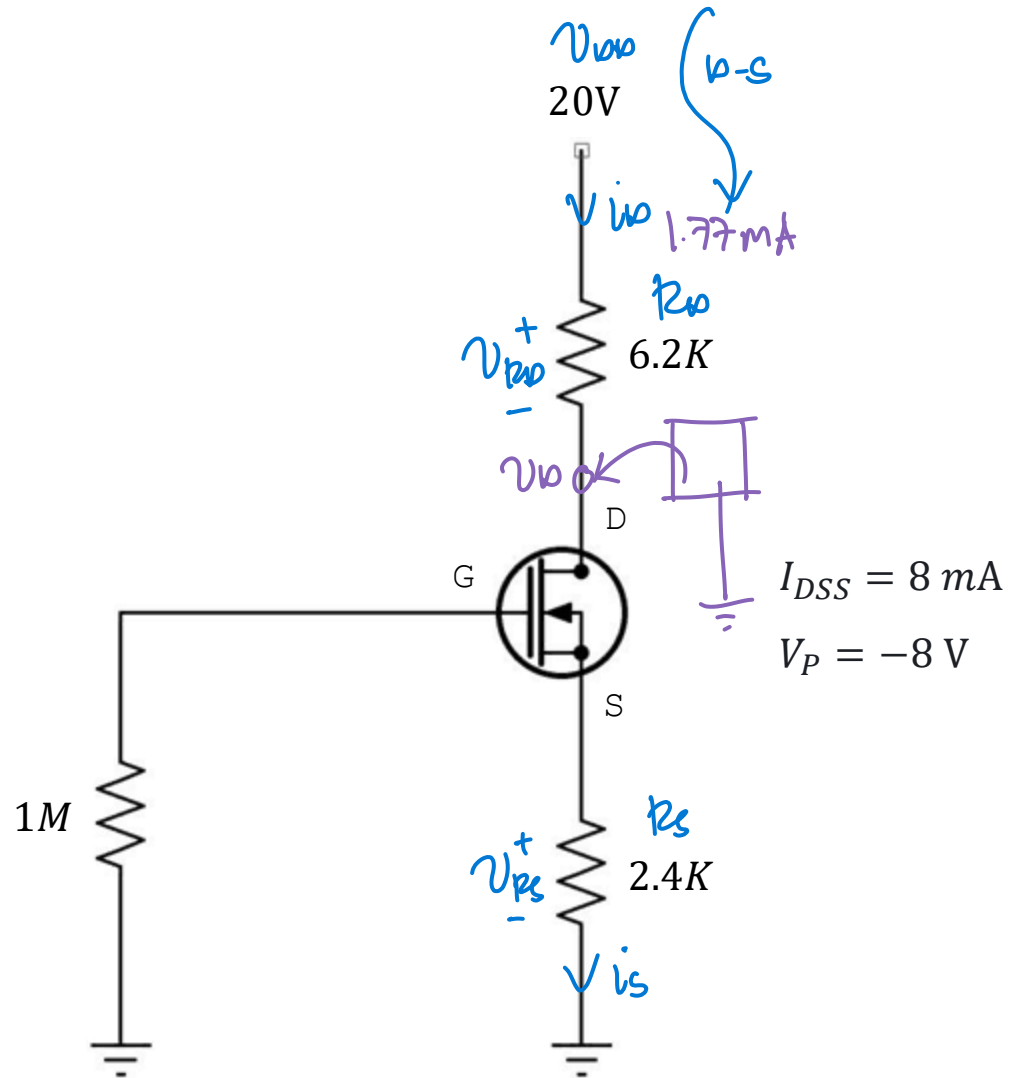
$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

$$i_D = 8 \text{ m} \left(1 - \frac{-4.24}{-8} \right)^2$$

$$i_{DQ} = 1.77 \text{ mA}$$

ans

EXERCISE



Solution

KVL @ D-S

$$-V_{DD} + V_{DS} + \underline{V_D} = 0$$

$$V_D = V_{DD} - V_{DS}$$

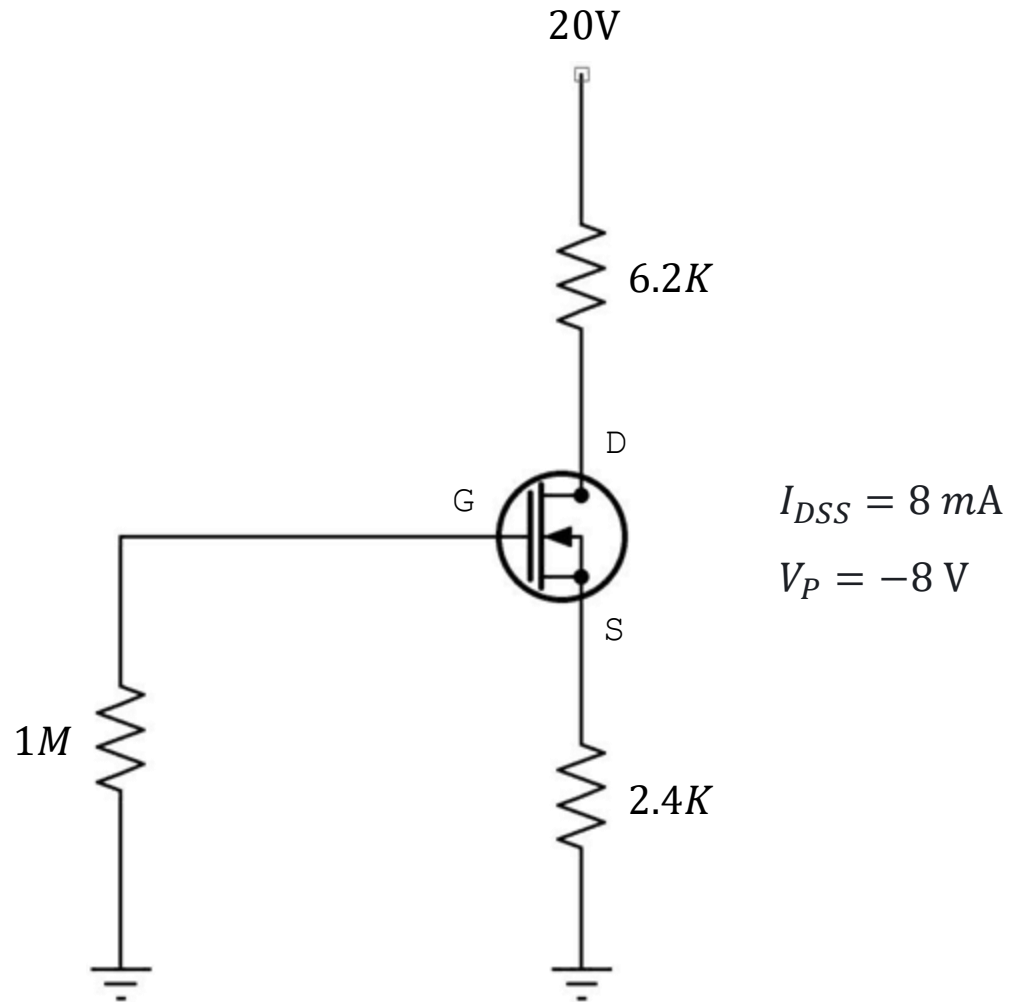
$$V_D = V_{DD} - I_D R_D$$

$$V_D = 20 - 1.77m(6.2k)$$

$$\boxed{V_D = 9.03V}$$

ans

EXERCISE



Solution

Transconductance Curve

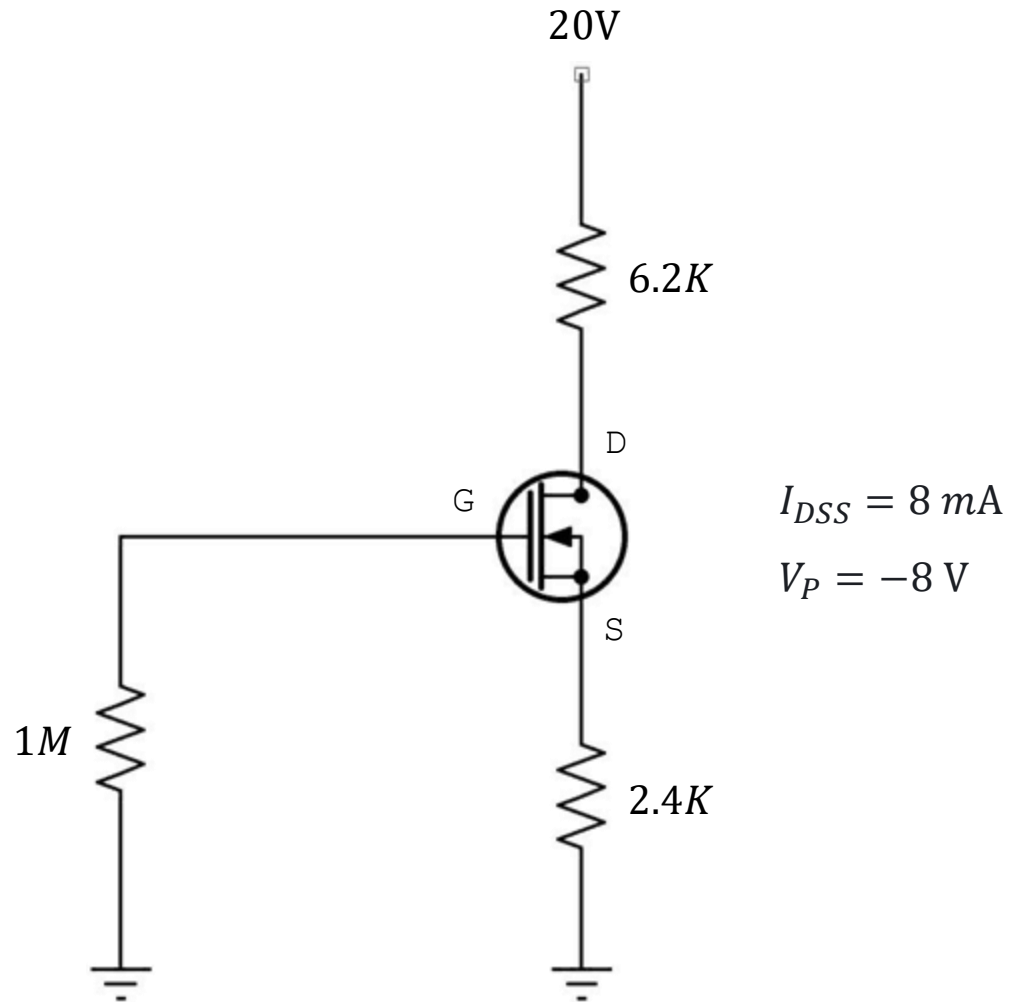
$$i_D = \frac{1}{4} I_{DSS} \mid v_{GS} = \frac{1}{2} V_P$$

$$i_D = \frac{1}{4} (8\text{ mA}) \mid v_{GS} = \frac{1}{2} (-8\text{ V})$$

$$\underline{i_D = 2\text{ mA} \mid v_{GS} = -4\text{ V}}$$



EXERCISE



Solution

$$V_{GS} = 0.3 V_P \mid i_D = \frac{1}{2} I_{DSS}$$

$$V_{GS} = 0.3(-8\text{V}) \mid i_D = \frac{1}{2}(8\text{mA})$$

$$\underline{V_{GS} = -2.4\text{V} \mid i_D = 4\text{mA}}$$

for $V_{GS} = 1\text{V}$

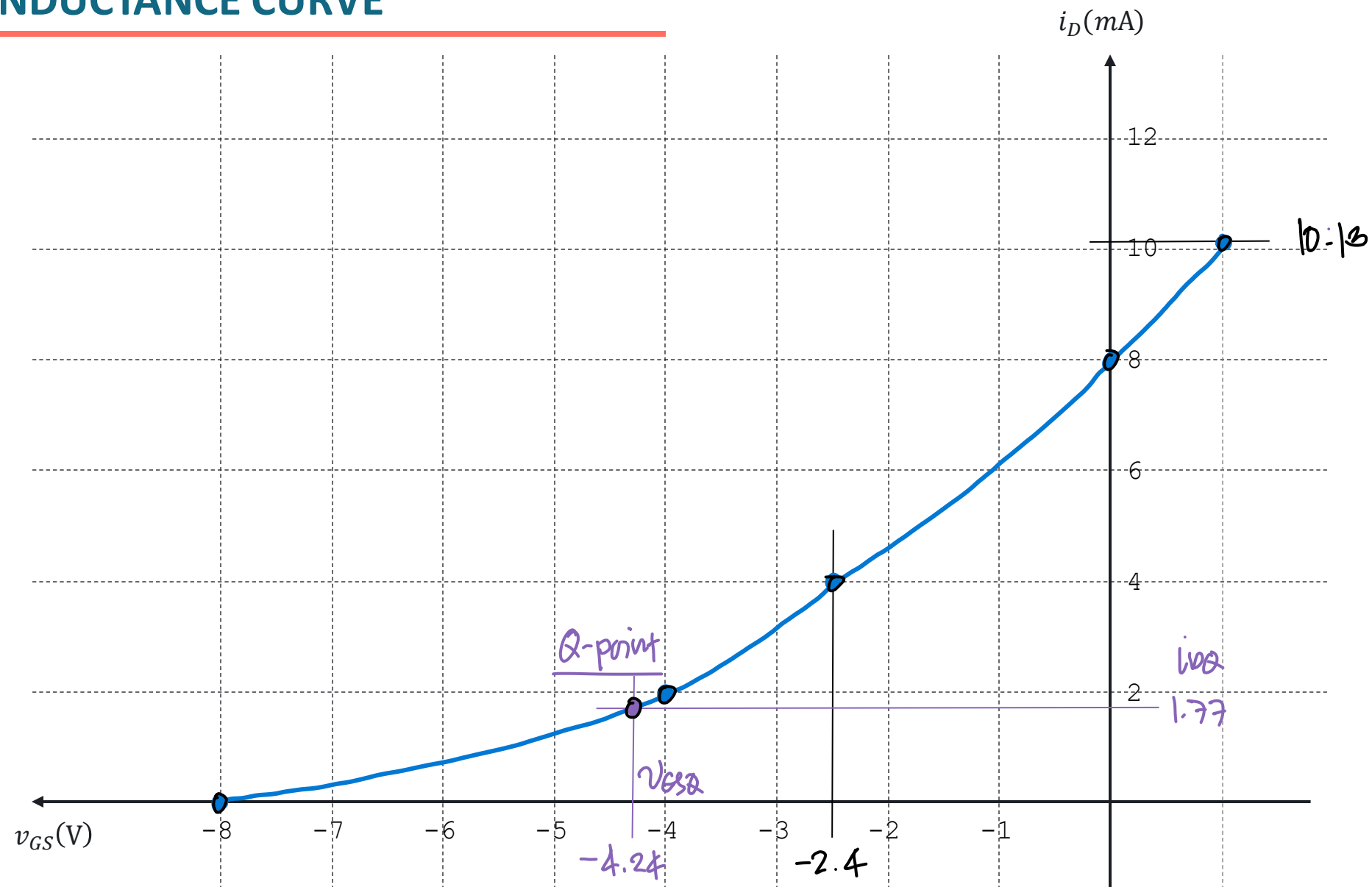
$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$i_D = 8\text{mA} \left(1 - \frac{1}{-8}\right)^2$$

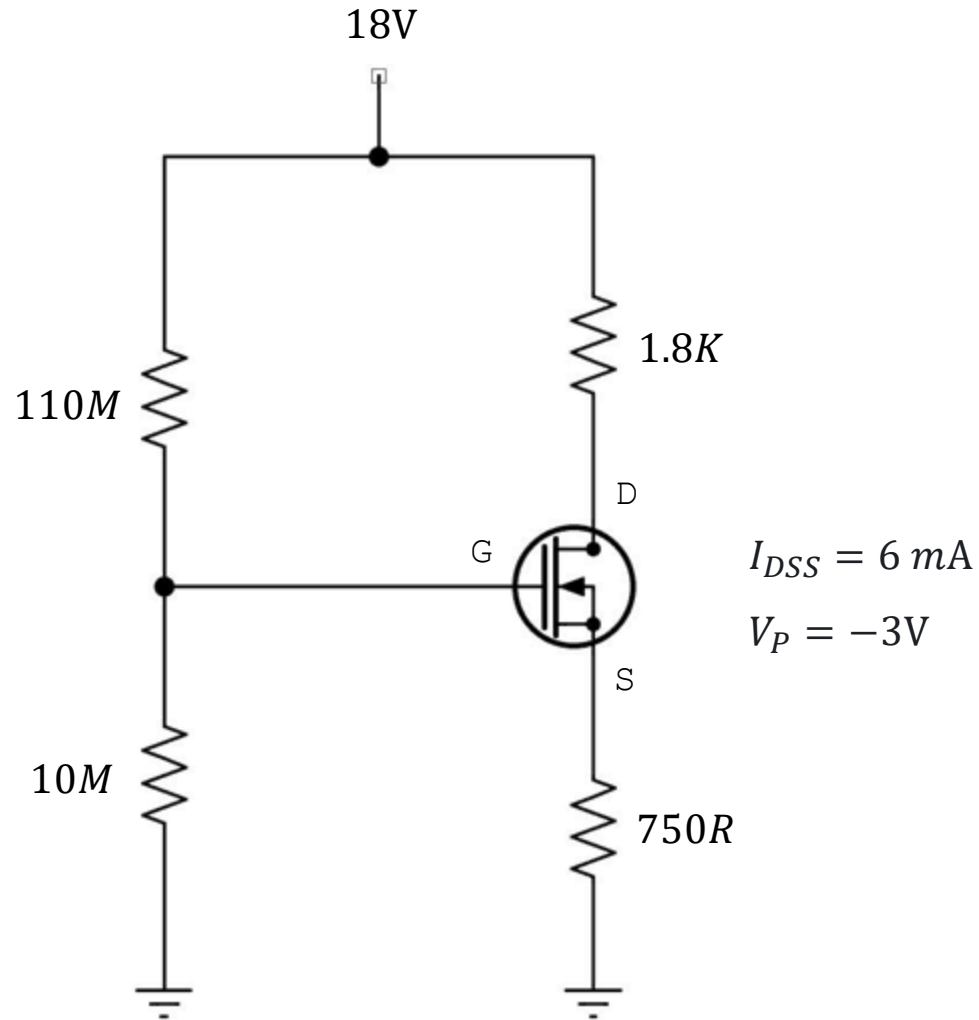
$$\underline{i_D = 10.13\text{mA}}$$



TRANSCONDUCTANCE CURVE



EXERCISE



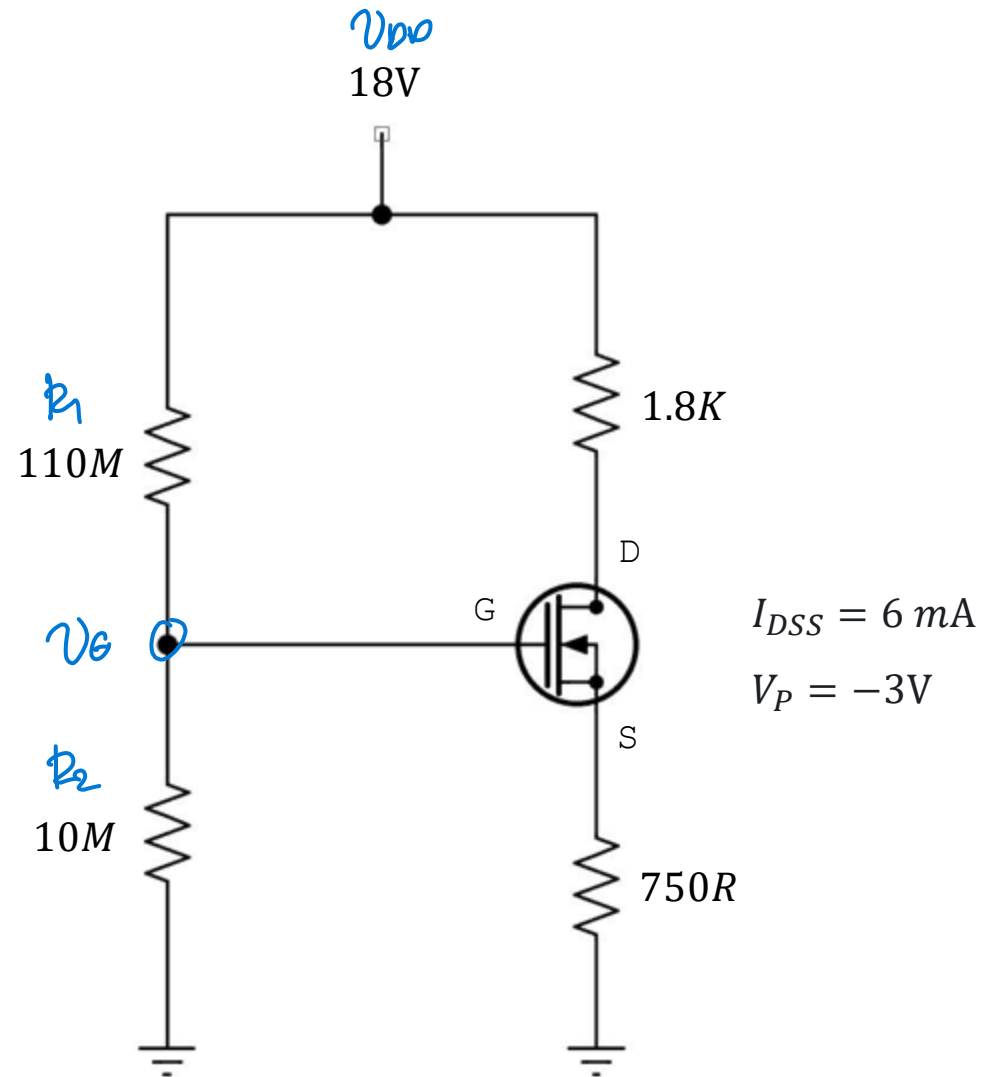
For the given network, determine the following:

- Gate-source voltage (v_{GSQ})
- Drain current (i_{DQ})
- Drain voltage (v_D)

and sketch the transconductance curve.



EXERCISE



Solution

by VDT

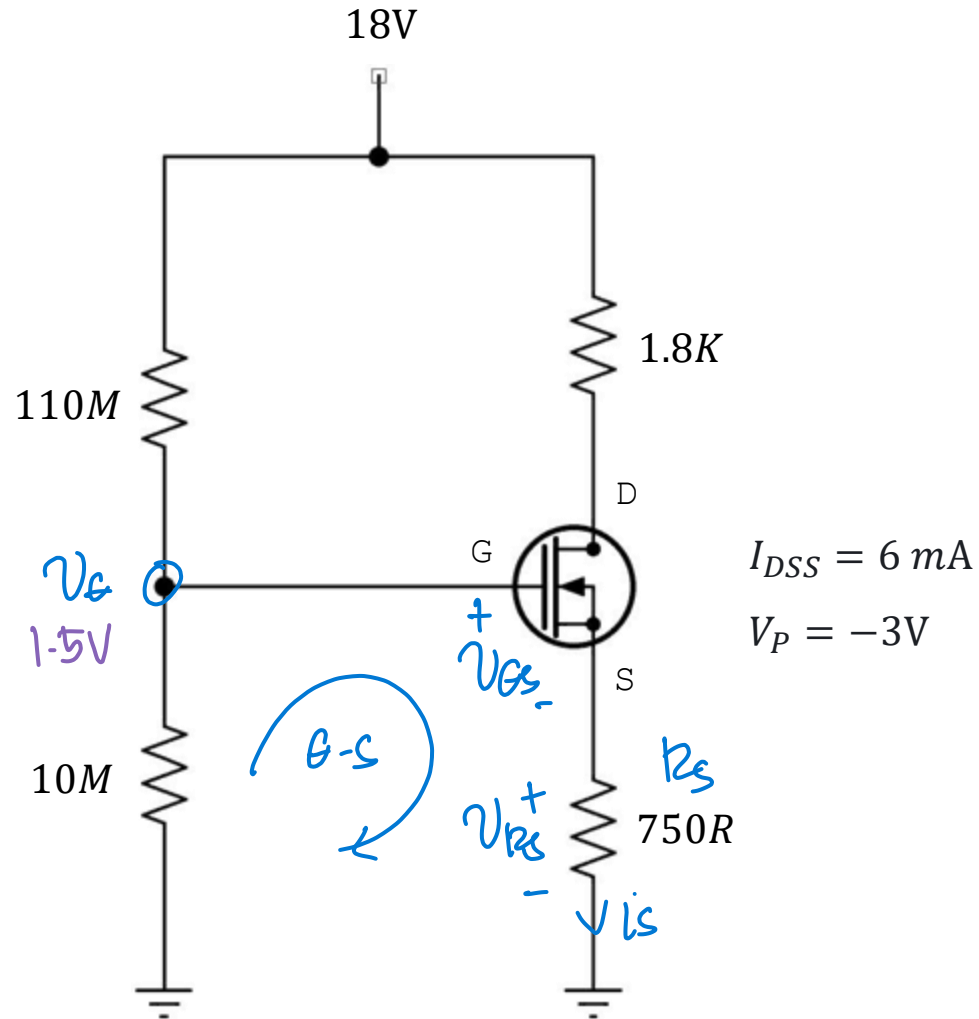
$$V_G = V_{DD} \frac{R_2}{R_1 + R_2}$$

$$V_G = 18 \frac{10M}{110M + 10M}$$

$$\underline{V_G = 1.5V}$$



EXERCISE



Solution

14V @ C-S

$$-V_G + \underline{V_{GS}} + V_{PS} = 0$$

$$V_{GS} = V_G - V_{PS}$$

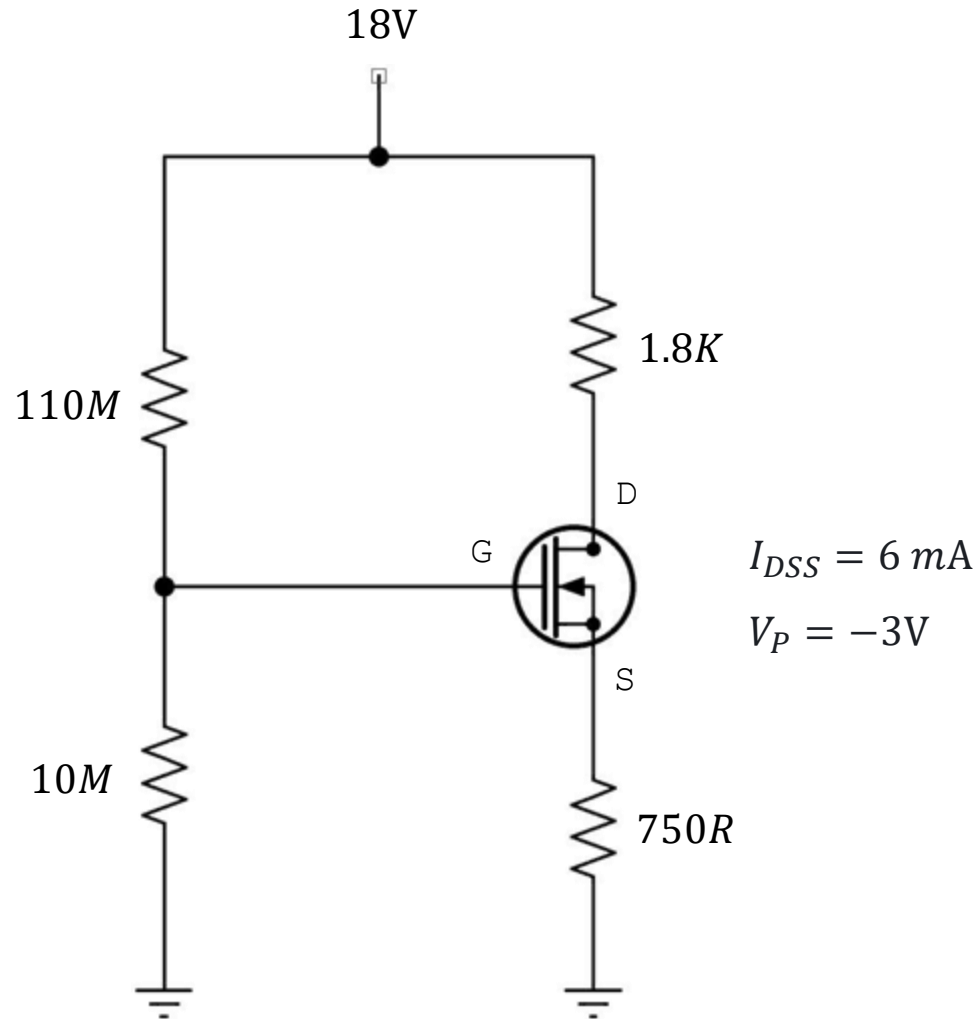
$$V_{GS} = V_G - \cancel{I_D} R_S \rightarrow I_D$$

$$V_{GS} = V_G - \underline{I_D} R_S$$

$$V_{GS} = V_G - I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 R_S$$

$$V_{GS} = V_G - I_{DSS} R_S \left(1 - \frac{2V_{GS}}{V_P} + \frac{V_{GS}^2}{V_P^2}\right)$$

EXERCISE



Solution

$$V_{GS} = 1.5 - (6 \text{ m} \cdot 750) \left[1 - \frac{2V_{GS}}{-3} + \frac{V_{GS}^2}{(-3)^2} \right]$$

$$V_{GS} = 1.5 - 4.5 \left(1 + \frac{2}{3} V_{GS} + \frac{1}{9} V_{GS}^2 \right)$$

$$\cancel{V_{GS}} = \cancel{1.5} - \cancel{4.5} - 3 \cancel{V_{GS}} - 0.5 \cancel{V_{GS}^2}$$

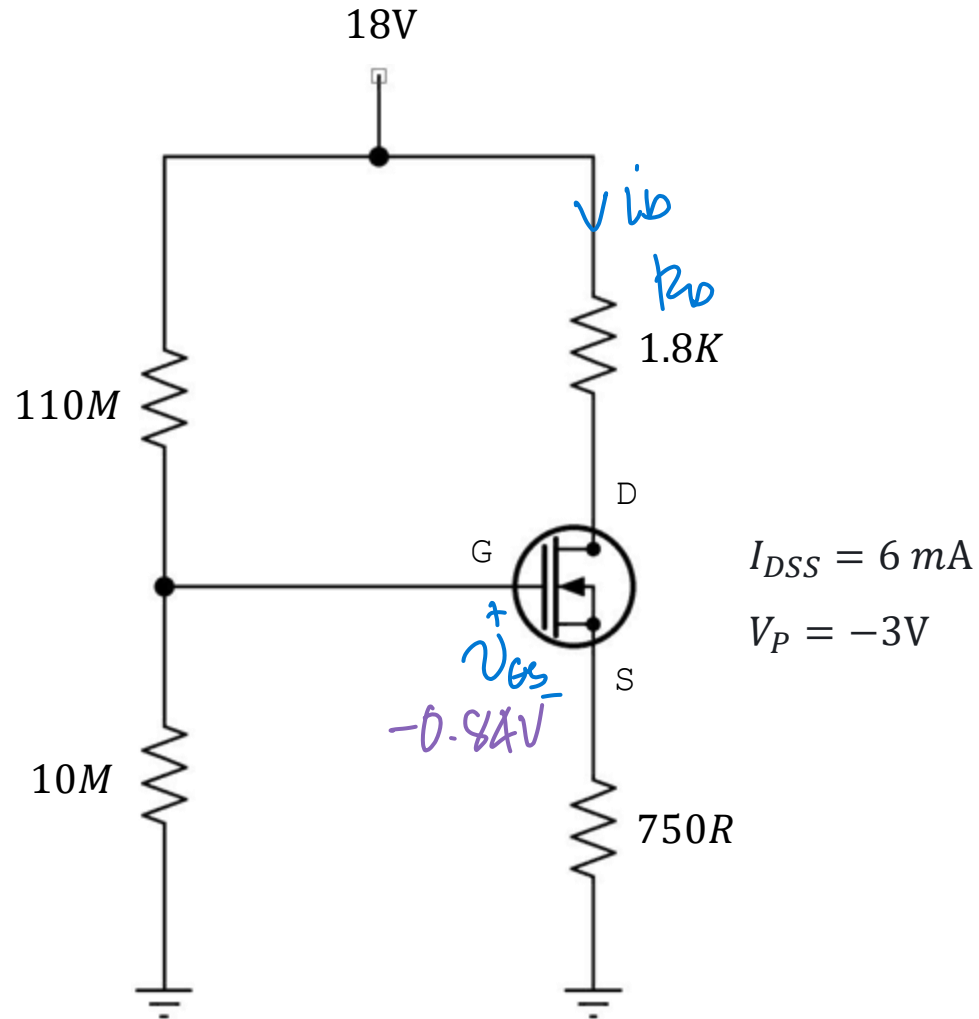
$$0 = -3 - 4V_{GS} - 0.5V_{GS}^2$$

$$V_{GS} = -7.16 \text{ V}$$

$$V_{GSQ} = -0.84 \text{ V}$$

Ans

EXERCISE



Solution

Shockley's Equation

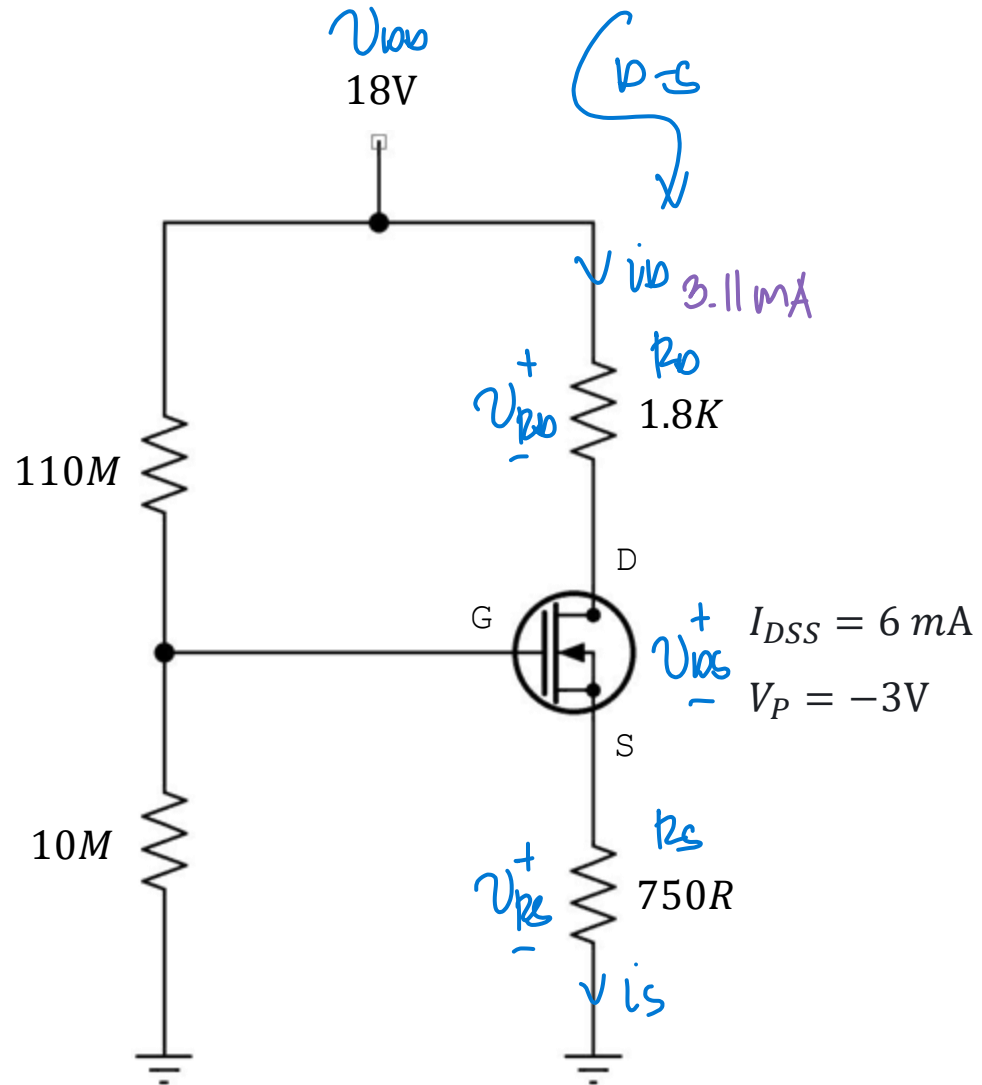
$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

$$i_D = 6 \text{ m} \left(1 - \frac{-0.84}{-3} \right)^2$$

$$i_{DQ} = 3.11 \text{ mA}$$

ans

EXERCISE



Solution

KVL @ D-S

$$-V_{DD} + V_{RD} + \underline{V_{DS}} + V_{RS} = 0$$

$$V_{DS} = V_{DD} - V_{RD} - V_{RS}$$

$$V_{DS} = V_{DD} - i_D R_D - i_S R_S$$

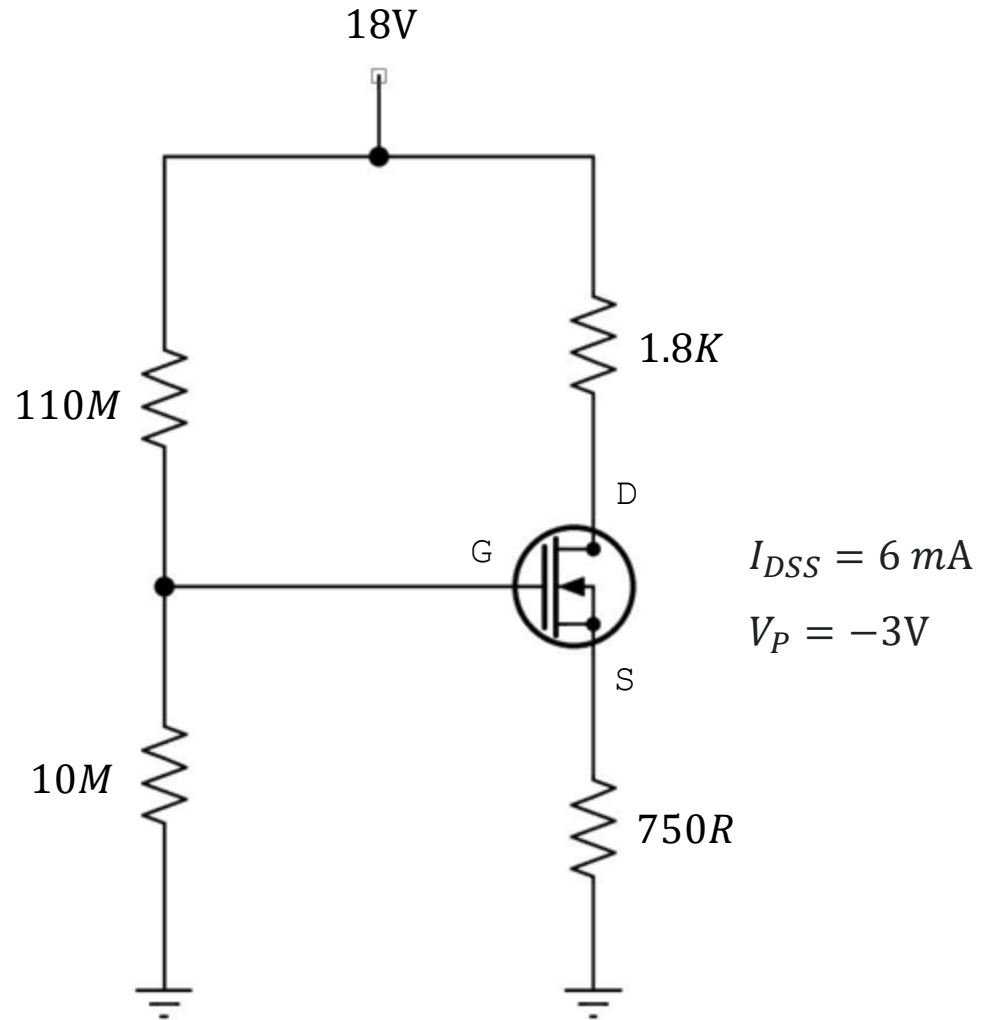
$$V_{DS} = V_{DD} - i_D (R_D + R_S)$$

$$V_{DS} = 18 - 3.11m(1.8k + 750)$$

$$V_{DS} = 10.07V$$

ans

EXERCISE



Solution

Transconductance Curve

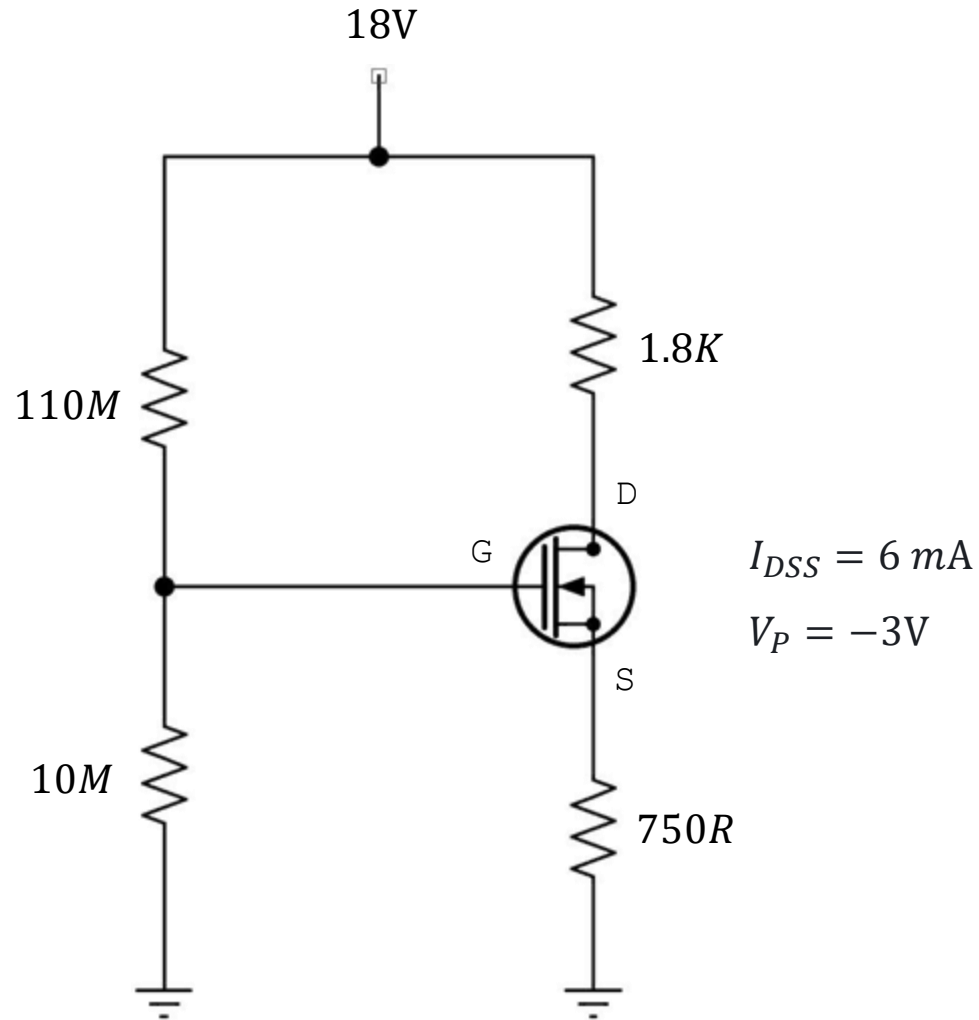
$$i_D = \frac{1}{4} I_{DSS} \mid v_{GS} = \frac{1}{2} V_P$$

$$i_D = \frac{1}{4} (6 \text{ mA}) \mid v_{GS} = \frac{1}{2} (-3V)$$

$$i_D = 3 \text{ mA} \mid v_{GS} = -1.5V$$



EXERCISE



Solution

$$V_{GS} = 0.3 V_P \mid i_D = \frac{1}{2} I_{DSS}$$

$$V_{GS} = 0.3(-3 \text{ V}) \mid i_D = \frac{1}{2}(6 \text{ mA})$$

$$\underline{V_{GS} = -0.9 \text{ V} \mid i_D = 3 \text{ mA}}$$

$$\underline{\text{for } V_{GS} = 1 \text{ V}}$$

$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

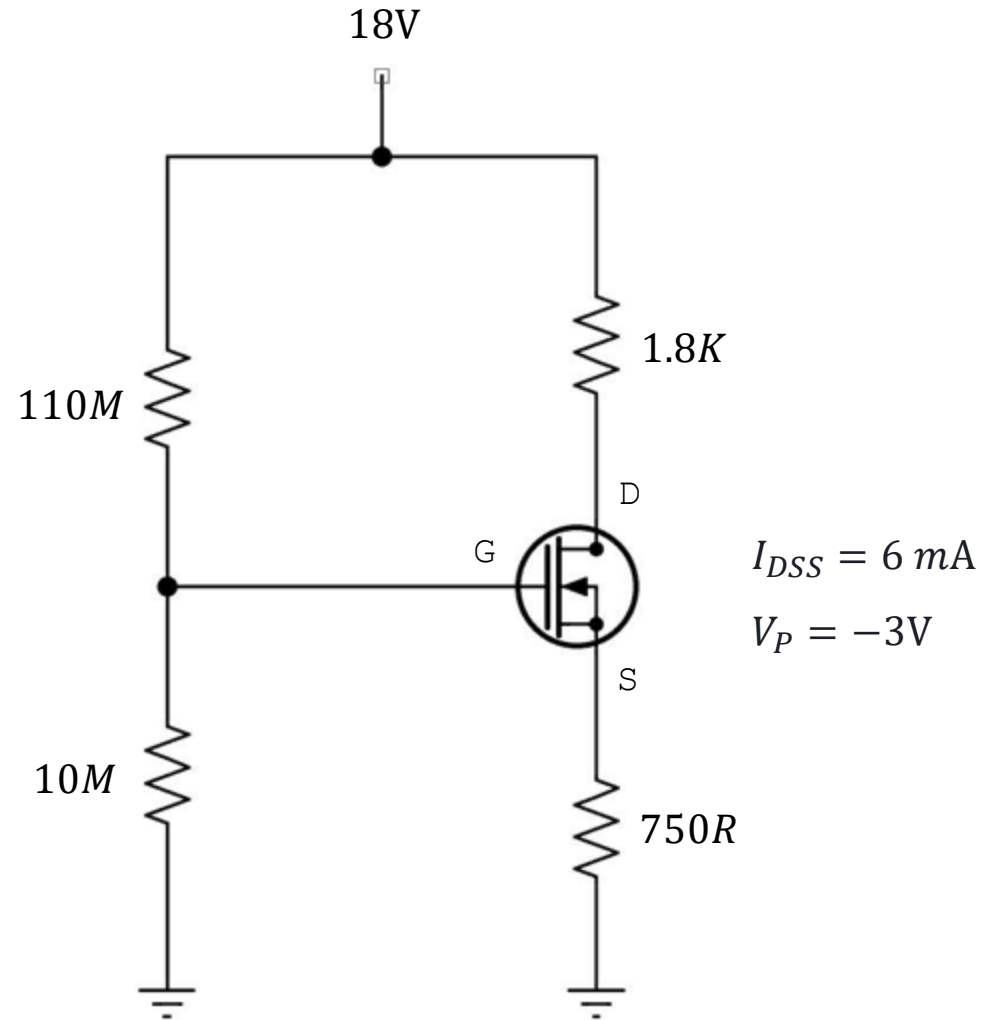
$$i_D = 6 \text{ mA} \left(1 - \frac{1}{-3} \right)^2$$

$$\underline{i_D = 10.67 \text{ mA}}$$

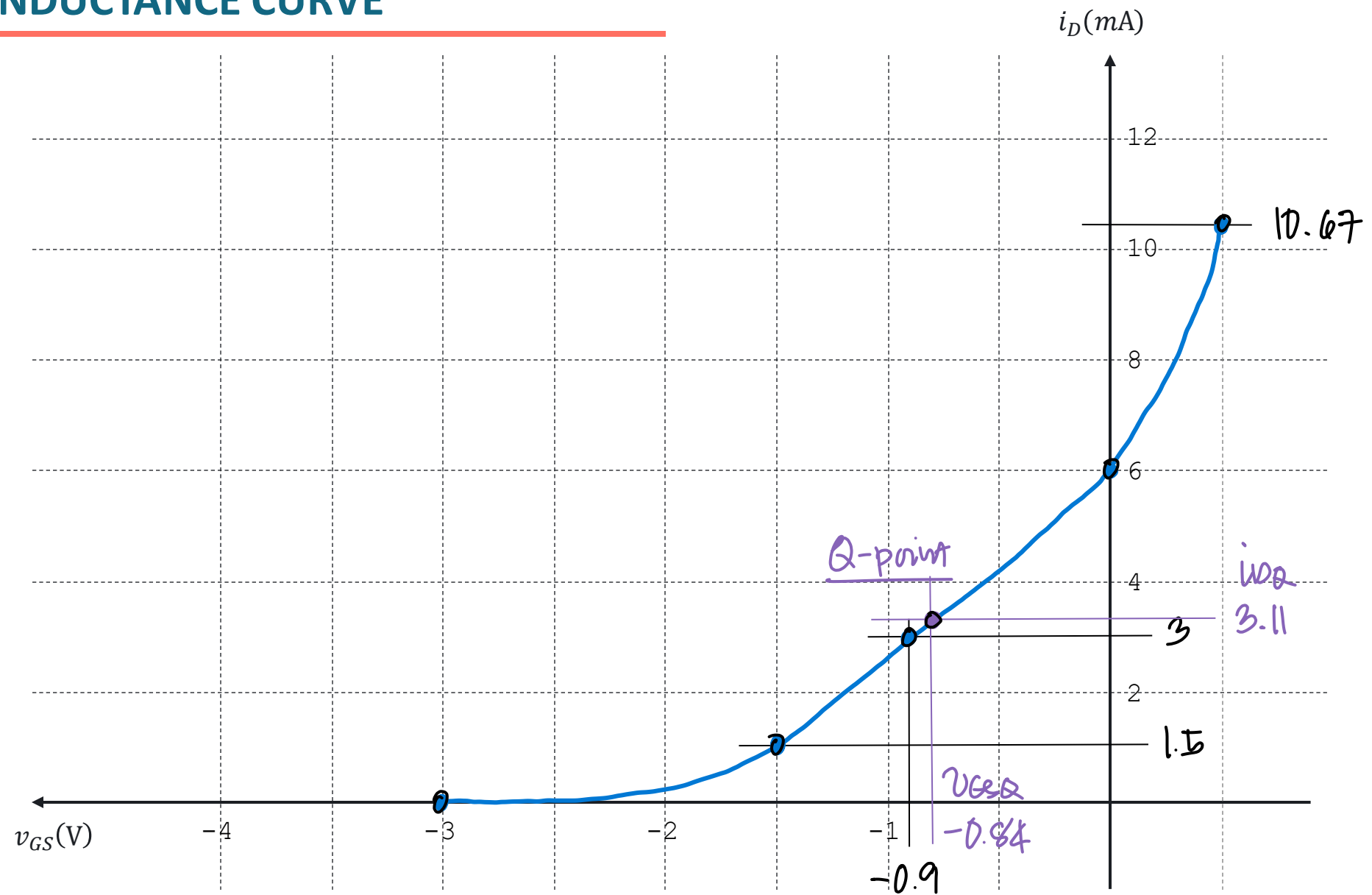


EXERCISE

Solution



TRANSCONDUCTANCE CURVE



LABORATORY

